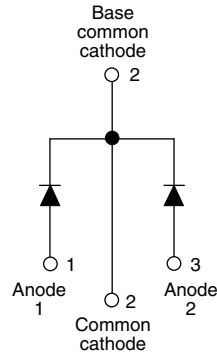


HEXFRED®

Ultrafast Soft Recovery Diode, 2 x 8 A


TO-247AC

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified for industrial level


RoHS
COMPLIANT

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA16PA60CPbF is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 8 A per leg continuous current, the VS-HFA16PA60CPbF is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to “snap-off” during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16PA60CPbF is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

PRODUCT SUMMARY

| | |
|-----------------|------------|
| Package | TO-247AC |
| $I_{F(AV)}$ | 2 x 8 A |
| V_R | 600 V |
| V_F at I_F | 1.7 V |
| t_{rr} (typ.) | 18 ns |
| T_J max. | 150 °C |
| Diode variation | Single die |

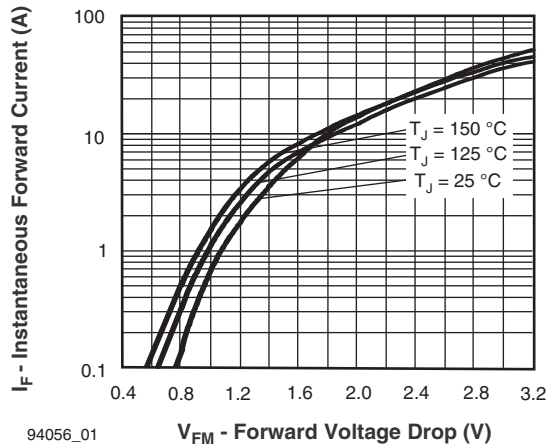
ABSOLUTE MAXIMUM RATINGS

| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
|--|----------------|---|---------------|-------|
| Cathode to anode voltage | V_R | | 600 | V |
| Maximum continuous forward current per leg per device | I_F | $T_C = 100\text{ °C}$ | 8 16 | A |
| Single pulse forward current | I_{FSM} | | 60 | |
| Maximum repetitive forward current | I_{FRM} | | 24 | |
| Maximum power dissipation | P_D | $T_C = 25\text{ °C}$ $T_C = 100\text{ °C}$ | 36 14 | |
| Operating junction and storage temperature range | T_J, T_{Stg} | | - 55 to + 150 | °C |

| ELECTRICAL SPECIFICATIONS PER LEG (T _J = 25 °C unless otherwise specified) | | | | | | |
|---|-----------------|--|------|------|------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Cathode to anode breakdown voltage | V _{BR} | I _R = 100 μA | 600 | - | - | V |
| Maximum forward voltage | V _{FM} | I _F = 8.0 A | - | 1.4 | 1.7 | |
| | | I _F = 16 A | - | 1.7 | 2.1 | |
| | | I _F = 8.0 A, T _J = 125 °C | - | 1.4 | 1.7 | |
| Maximum reverse leakage current | I _{RM} | V _R = V _R rated | - | 0.3 | 5.0 | μA |
| | | T _J = 125 °C, V _R = 0.8 x V _R rated | - | 100 | 500 | |
| Junction capacitance | C _T | V _R = 200 V | - | 10 | 25 | pF |
| Series inductance | L _S | Measured lead to lead 5 mm from package body | - | 8.0 | - | nH |

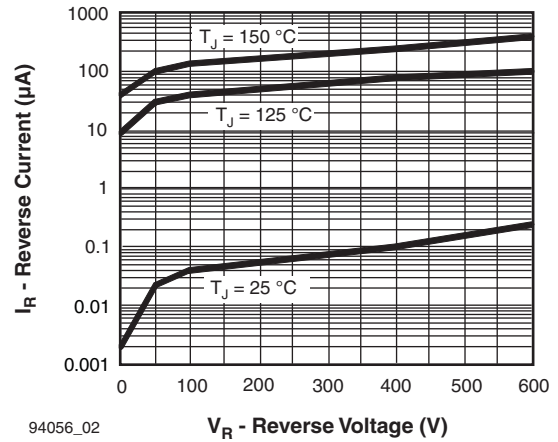
| DYNAMIC RECOVERY CHARACTERISTICS PER LEG (T _J = 25 °C unless otherwise specified) | | | | | | |
|--|---------------------------|---|------|------|------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Reverse recovery time See fig. 5, 6 and 16 | t _{rr} | I _F = 1.0 A, di _F /dt = 200 A/μs, V _R = 30 V | - | 18 | - | ns |
| | t _{rr1} | T _J = 25 °C | - | 37 | 55 | |
| | t _{rr2} | T _J = 125 °C | - | 55 | 90 | |
| Peak recovery current See fig. 7 and 8 | I _{RRM1} | T _J = 25 °C | - | 3.5 | 5.0 | A |
| | I _{RRM2} | T _J = 125 °C | - | 4.5 | 8.0 | |
| Reverse recovery charge See fig. 9 and 10 | Q _{rr1} | T _J = 25 °C | - | 65 | 138 | nC |
| | Q _{rr2} | T _J = 125 °C | - | 124 | 360 | |
| Peak rate of fall recovery current during t _b See fig. 11 and 12 | di _{(rec)M} /dt1 | T _J = 25 °C | - | 240 | - | A/μs |
| | di _{(rec)M} /dt2 | T _J = 125 °C | - | 210 | - | |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | |
|---|-------------------|--|--------------|------|------------|------------------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Lead temperature | T _{lead} | 0.063" from case (1.6 mm) for 10 s | - | - | 300 | °C |
| Junction to case, single leg conducting | R _{thJC} | | - | - | 3.5 | K/W |
| Junction to case, both leg conducting | | | - | - | 1.75 | |
| Thermal resistance, junction to ambient | R _{thJA} | Typical socket mount | - | - | 40 | |
| Thermal resistance, case to heatsink | R _{thCS} | Mounting surface, flat, smooth and greased | - | 0.25 | - | |
| Weight | | | - | 6.0 | - | g |
| | | | - | 0.21 | - | oz. |
| Mounting torque | | | 6.0 (5.0) | - | 12 (10) | kgf · cm (lbf · in) |
| Marking device | | Case style TO-247AC (JEDEC) | HFA16PA60C | | | |



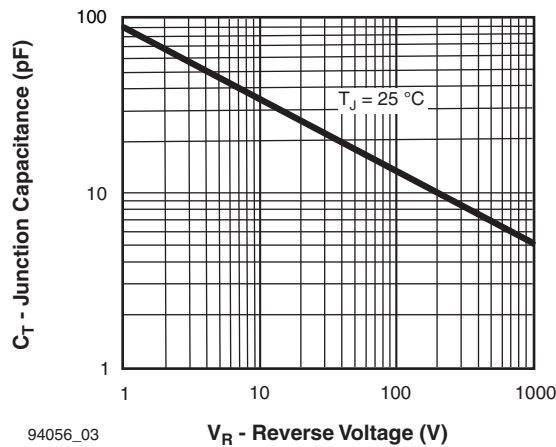
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Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current (Per Leg)



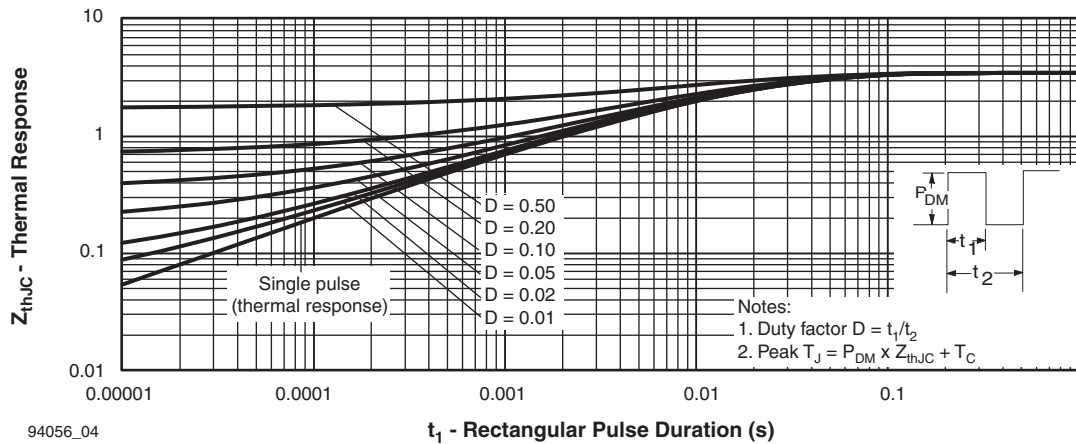
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Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Leg)



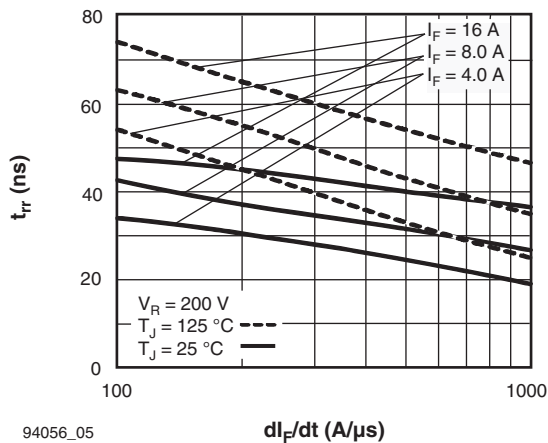
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Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)



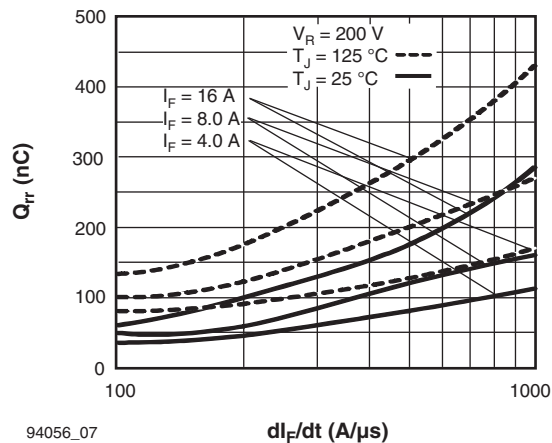
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Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)



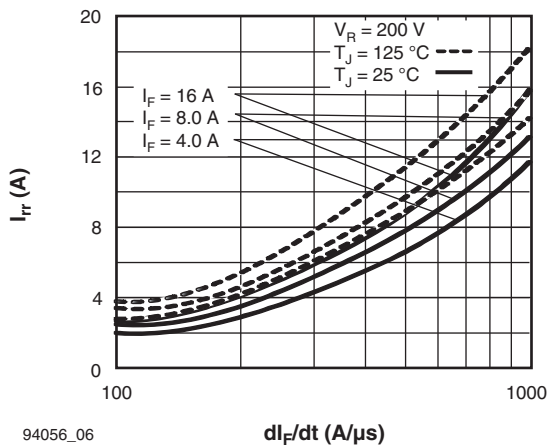
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Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt (Per Leg)



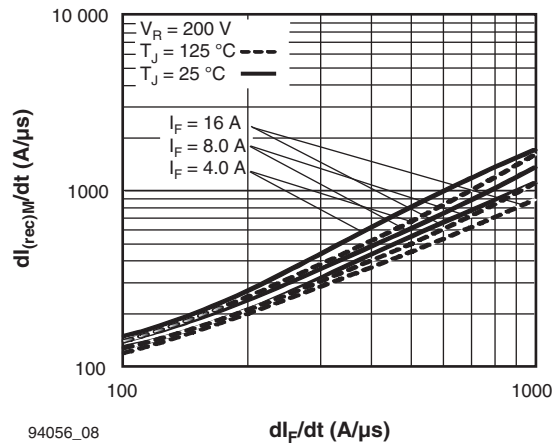
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Fig. 7 - Typical Stored Charge vs. dI_F/dt (Per Leg)



94056_06

Fig. 6 - Typical Recovery Current vs. dI_F/dt (Per Leg)



94056_08

Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt (Per Leg)

HEXFRED®
 Ultrafast Soft Recovery Diode, 2 x 8 A

Vishay Semiconductors

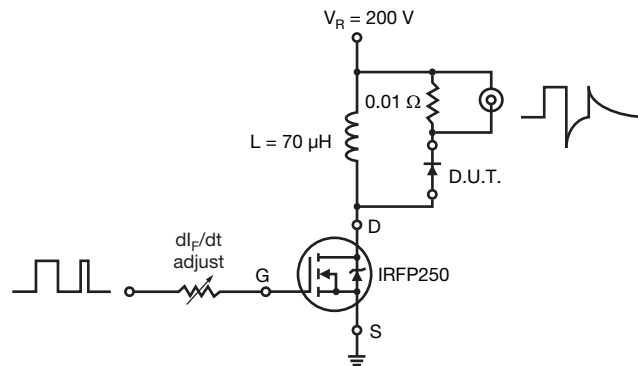
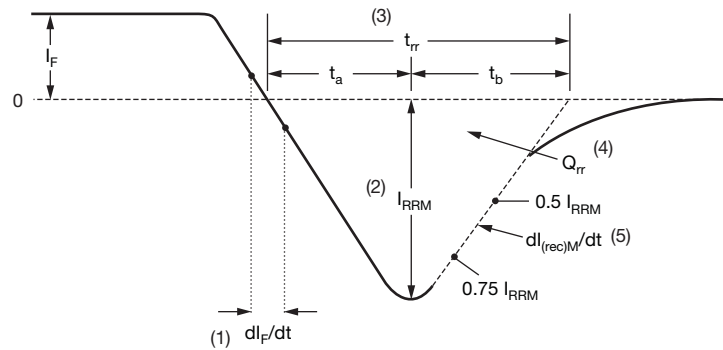


Fig. 9 - Reverse Recovery Parameter Test Circuit


 (1) di_F/dt - rate of change of current through zero crossing

 (2) I_{RRM} - peak reverse recovery current

 (3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through $0.75 I_{RRM}$ and $0.50 I_{RRM}$ extrapolated to zero current.

 (4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

 (5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

VS-HFA16PA60CPbF



Vishay Semiconductors

HEXFRED®
Ultrafast Soft Recovery Diode, 2 x 8 A

ORDERING INFORMATION TABLE

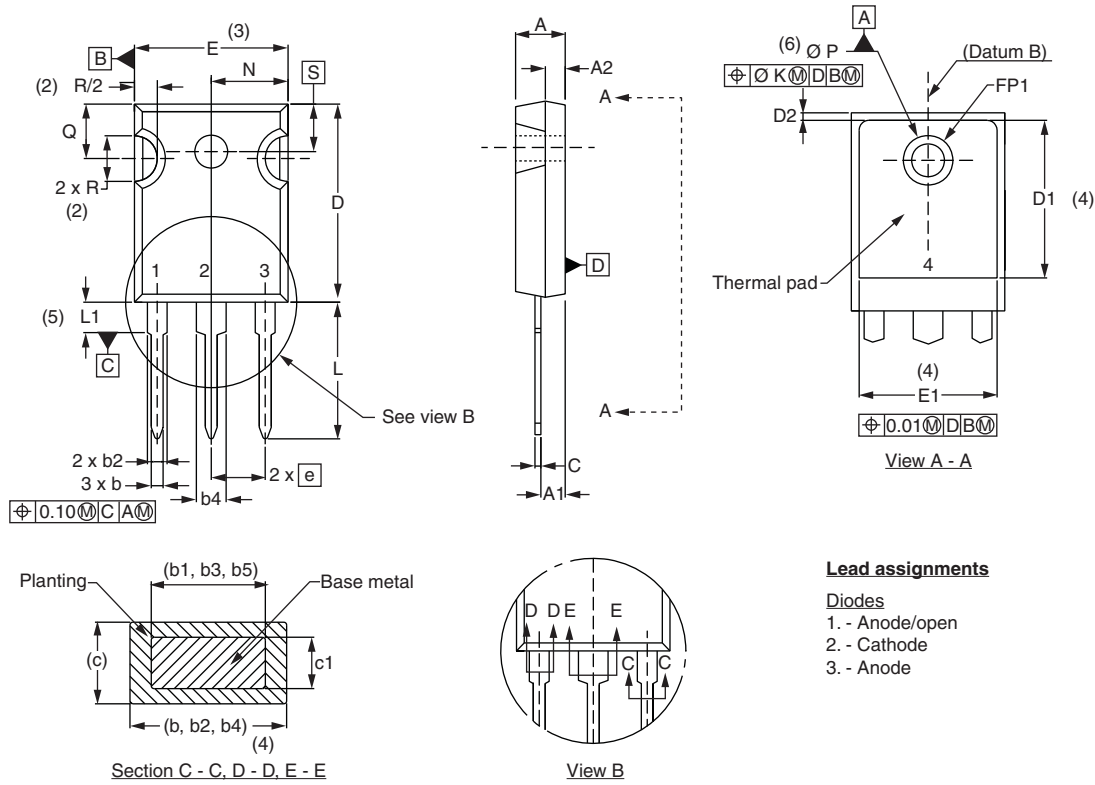
| | | | | | | | | |
|-------------|-----|----|---|----|----|----|---|-----|
| Device code | VS- | HF | A | 16 | PA | 60 | C | PbF |
| | ① | ② | ③ | ④ | ⑤ | ⑥ | ⑦ | ⑧ |

- 1** - Vishay Semiconductors product
- 2** - HEXFRED® family
- 3** - Electron irradiated
- 4** - Current rating (16 = 16 A)
- 5** - PA = TO-247AC
- 6** - Voltage rating: (60 = 600 V)
- 7** - Circuit configuration
C = Common cathode
- 8** - PbF = Lead (Pb)-free

| LINKS TO RELATED DOCUMENTS | |
|----------------------------|--|
| Dimensions | www.vishay.com/doc?95223 |
| Part marking information | www.vishay.com/doc?95226 |



DIMENSIONS in millimeters and inches



Lead assignments

- Diodes**
 1. - Anode/open
 2. - Cathode
 3. - Anode

| SYMBOL | MILLIMETERS | | INCHES | | NOTES | SYMBOL | MILLIMETERS | | INCHES | | NOTES |
|--------|-------------|-------|--------|-------|-------|--------|-------------|-------|-----------|-------|-------|
| | MIN. | MAX. | MIN. | MAX. | | | MIN. | MAX. | MIN. | MAX. | |
| A | 4.65 | 5.31 | 0.183 | 0.209 | | D2 | 0.51 | 1.30 | 0.020 | 0.051 | |
| A1 | 2.21 | 2.59 | 0.087 | 0.102 | | E | 15.29 | 15.87 | 0.602 | 0.625 | 3 |
| A2 | 1.50 | 2.49 | 0.059 | 0.098 | | E1 | 13.72 | - | 0.540 | - | |
| b | 0.99 | 1.40 | 0.039 | 0.055 | | e | 5.46 BSC | | 0.215 BSC | | |
| b1 | 0.99 | 1.35 | 0.039 | 0.053 | | FK | 2.54 | | 0.010 | | |
| b2 | 1.65 | 2.39 | 0.065 | 0.094 | | L | 14.20 | 16.10 | 0.559 | 0.634 | |
| b3 | 1.65 | 2.37 | 0.065 | 0.094 | | L1 | 3.71 | 4.29 | 0.146 | 0.169 | |
| b4 | 2.59 | 3.43 | 0.102 | 0.135 | | N | 7.62 BSC | | 0.3 | | |
| b5 | 2.59 | 3.38 | 0.102 | 0.133 | | ØP | 3.56 | 3.66 | 0.14 | 0.144 | |
| c | 0.38 | 0.86 | 0.015 | 0.034 | | ØP1 | - | 6.98 | - | 0.275 | |
| c1 | 0.38 | 0.76 | 0.015 | 0.030 | | Q | 5.31 | 5.69 | 0.209 | 0.224 | |
| D | 19.71 | 20.70 | 0.776 | 0.815 | 3 | R | 4.52 | 5.49 | 1.78 | 0.216 | |
| D1 | 13.08 | - | 0.515 | - | 4 | S | 5.51 BSC | | 0.217 BSC | | |

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c



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